

L Number	Hits	Search Text	DB	Time stamp
1	0	EEPROM and Flash and memory and etch and floating and control and gate and oxide and opening and CMP and (substantially adj uniform adj width)	USPAT	2004/08/25 12:18
2	178	EEPROM and Flash and memory and etch and floating and control and gate and oxide and opening and CMP	USPAT	2004/08/25 12:18
3	0	(EEPROM and Flash and memory and etch and floating and control and gate and oxide and opening and CMP) and (uniform adj width)	USPAT	2004/08/25 12:19
4	14	(EEPROM and Flash and memory and etch and floating and control and gate and oxide and opening and CMP) and isotropic and width and dry	USPAT	2004/08/25 12:36
5	1	("6773989").PN.	USPAT	2004/08/25 12:37
6	1	("6727545").PN.	USPAT	2004/08/25 12:37
7	1	("6627946").PN.	USPAT	2004/08/25 12:37
8	1	("6433382").PN.	USPAT	2004/08/25 12:37
9	1	((("6773989").PN.) and (EEPROM or Flash or opening or trench or first or second or third or control or floating or gate or oxide or coupling or bigger or width or narrow or contour or portion or drain or source or memory or device or CMP or expose or exposing or exposed or isotropic or anisotropic or dry or gas or etch or etching or underneath or dielectric or uniform or substantially))	USPAT	2004/08/25 13:00
10	1	((("6727545").PN.) and (EEPROM or Flash or opening or trench or first or second or third or control or floating or gate or oxide or coupling or bigger or width or narrow or contour or portion or drain or source or memory or device or CMP or expose or exposing or exposed or isotropic or anisotropic or dry or gas or etch or etching or underneath or dielectric or uniform or substantially))	USPAT	2004/08/25 13:06
11	1	((("6627946").PN.) and (EEPROM or Flash or opening or trench or first or second or third or control or floating or gate or oxide or coupling or bigger or width or narrow or contour or portion or drain or source or memory or device or CMP or expose or exposing or exposed or isotropic or anisotropic or dry or gas or etch or etching or underneath or dielectric or uniform or substantially))	USPAT	2004/08/25 13:06
12	1	((("6433382").PN.) and (EEPROM or Flash or opening or trench or first or second or third or control or floating or gate or oxide or coupling or bigger or width or narrow or contour or portion or drain or source or memory or device or CMP or expose or exposing or exposed or isotropic or anisotropic or dry or gas or etch or etching or underneath or dielectric or uniform or substantially))	USPAT	2004/08/25 13:13
13	2279	438/257	USPAT	2004/08/25 13:13
14	857	438/259	USPAT	2004/08/25 13:14
15	508	438/267	USPAT	2004/08/25 13:14
16	982	438/270	USPAT	2004/08/25 13:14
17	1035	438/299	USPAT	2004/08/25 13:14
18	851	438/300	USPAT	2004/08/25 13:14
19	1859	438/301	USPAT	2004/08/25 13:14
20	688	438/593	USPAT	2004/08/25 13:14
21	548	438/589	USPAT	2004/08/25 13:14
22	2919	438/637	USPAT	2004/08/25 13:14
23	3147	438/692	USPAT	2004/08/25 13:14
24	1353	438/700	USPAT	2004/08/25 13:14
25	1618	438/706	USPAT	2004/08/25 13:15
26	818	438/712	USPAT	2004/08/25 13:15
27	342	438/739	USPAT	2004/08/25 13:15
28	519	438/740	USPAT	2004/08/25 13:15

8/25/04